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(54) Title: METHOD AND APPARATUS FOR CONTROLLING THE TEMPERATURE OF A SEMICONDUCTOR WAFER

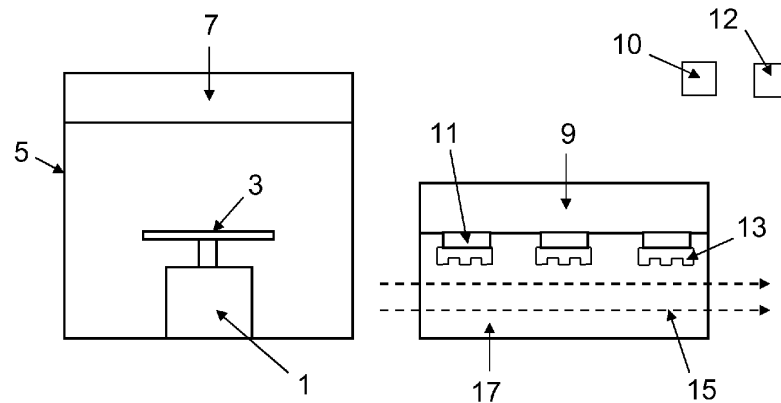


FIG. 1

(57) Abstract: A semiconductor wafer mass metrology method comprising: controlling the temperature of a semiconductor wafer by: detecting information relating to the temperature of the semiconductor wafer; and controlling cooling or heating of the semiconductor wafer based on the detected information relating to the temperature of the semiconductor wafer; wherein controlling the cooling or heating of the semiconductor wafer comprises controlling a duration of the cooling or heating of the semiconductor wafer; and subsequently loading the semiconductor wafer onto a measurement area of a semiconductor wafer mass metrology apparatus.

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